N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

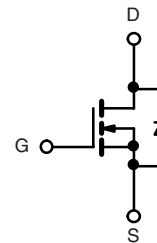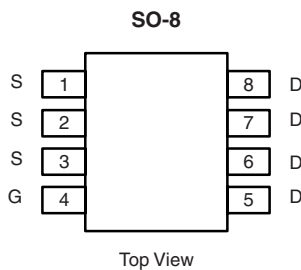| V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[d]	Q_g (Typ.)
60	0.036 at V_{GS} = 10 V	8	10.5 nC
	0.043 at V_{GS} = 4.5 V	8	

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Optimized for "Low Side" Synchronous Rectifier Operation
- 100 % R_g and UIS Tested

RoHS
COMPLIANT

HALOGEN
FREE
Available

APPLICATIONS

- CCFL Inverter

SO-8

S 1	8 D
S 2	7 D
S 3	6 D
G 4	5 D

Top View

Ordering Information: Si4436DY-T1-E3 (Lead (Pb)-free)
Si4436DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	8[a]	A
	T_C = 70 °C		6.8	
	T_A = 25 °C		6.1[b, c]	
	T_A = 70 °C		4.8[b, c]	
Pulsed Drain Current		I_{DM}	25	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	4.2	
	T_A = 25 °C		2.1[b, c]	
Avalanche Current	L = 0.1 mH	I_{AS}	15	
Single-Pulse Avalanche Energy		E_{AS}	11.2	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	5	W
	T_C = 70 °C		3.2	
	T_A = 25 °C		2.5[b, c]	
	T_A = 70 °C		1.6[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	38	50	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	20	25	

Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under Steady State conditions is 85 °C/W.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted

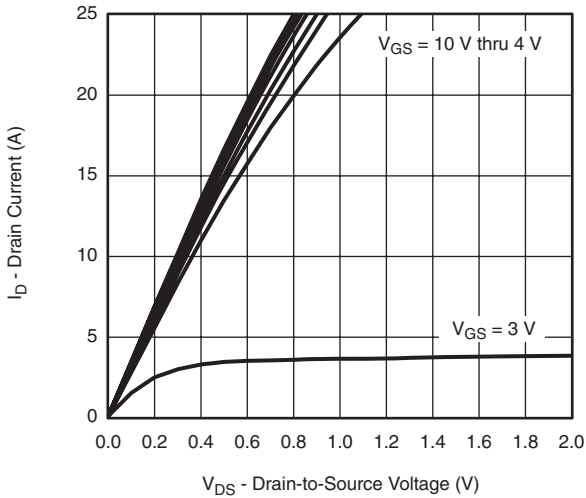| Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	60			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		55		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.5		2.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	25			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 4.6 A		0.030	0.036	Ω
		V_{GS} = 4.5 V, I_D = 4.2 A		0.035	0.043	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 4.6 A		20		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 30 V, V_{GS} = 0 V, f = 1 MHz		1100		pF
Output Capacitance	C_{oss}			90		
Reverse Transfer Capacitance	C_{rss}			55		
Total Gate Charge	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 4.6 A		21	32	nC
		V_{DS} = 30 V, V_{GS} = 4.5 V, I_D = 4.6 A		10.5	16	
Gate-Source Charge	Q_{gs}			3.5		
Gate-Drain Charge	Q_{gd}			4.2		
Gate Resistance	R_g	f = 1 MHz		3.3	5	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 30 V, R_L = 5.4 Ω $I_D \cong$ 5.6 A, V_{GEN} = 4.5 V, R_g = 1 Ω		20	30	ns
Rise Time	t_r			150	225	
Turn-Off DelayTime	$t_{d(off)}$			20	30	
Fall Time	t_f			60	90	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 30 V, R_L = 5.4 Ω $I_D \cong$ 5.6 A, V_{GEN} = 10 V, R_g = 1 Ω		10	15	
Rise Time	t_r			15	25	
Turn-Off DelayTime	$t_{d(off)}$			25	40	
Fall Time	t_f			10	15	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I_S	T_C = 25 °C			4.2	A
Pulse Diode Forward Current[a]	I_{SM}				25	
Body Diode Voltage	V_{SD}	I_S = 2 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 5.5 A, dI/dt = 100 A/µs, T_J = 25 °C		25	50	ns
Body Diode Reverse Recovery Charge	Q_{rr}			25	50	nC
Reverse Recovery Fall Time	t_a			19		ns
Reverse Recovery Rise Time	t_b			6		

Notes:
a. Pulse test; pulse width $\leq$ 300 µs, duty cycle $\leq$ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
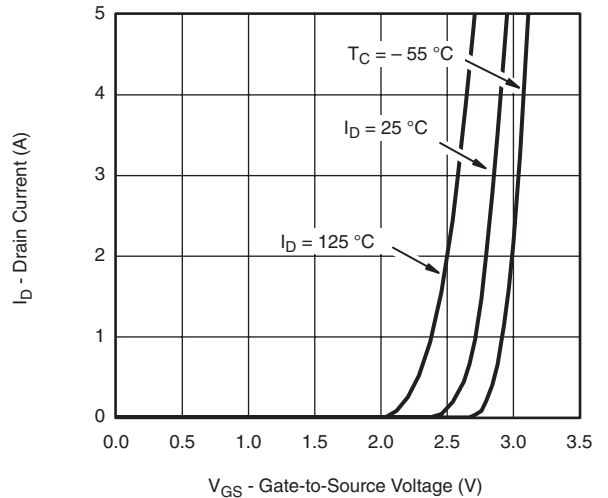
Si4436DY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

V_{GS} = 10 V thru 4 V

V_{GS} = 3 V

I_D - Drain Current (A)

V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics

$T_C = -55$ °C

I_D = 25 °C

I_D = 125 °C

I_D - Drain Current (A)

V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics

V_{GS} = 4.5 V

V_{GS} = 10 V

$R_{DS(on)}$ - On-Resistance (Ω)
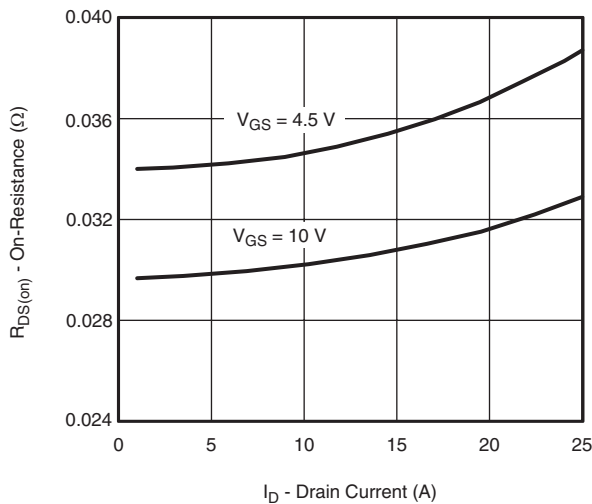
I_D - Drain Current (A)

On-Resistance vs. Drain Current

C_{iss}

C_{oss}

C_{rss}

C - Capacitance (pF)

V_{DS} - Drain-to-Source Voltage (V)

Capacitance

I_D = 4.6 A

V_{DS} = 30 V

V_{DS} = 48 V

V_{GS} - Gate-to-Source Voltage (V)

Q_g - Total Gate Charge (nC)

Gate Charge

V_{GS} = 10 V,
I_D = 4.6 A

$R_{DS(on)}$ - On-Resistance
(Normalized)
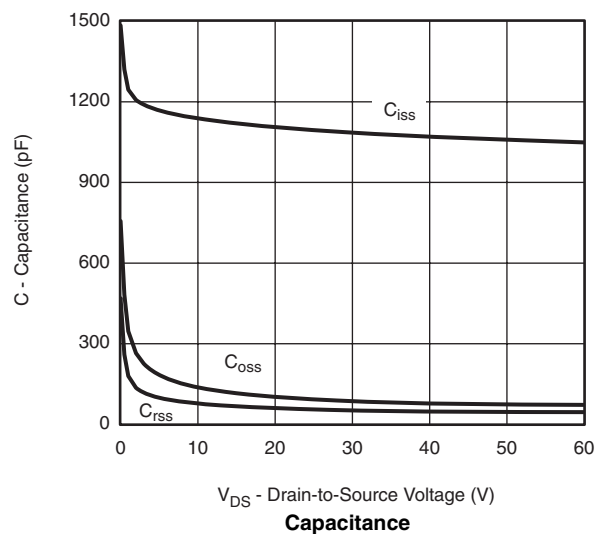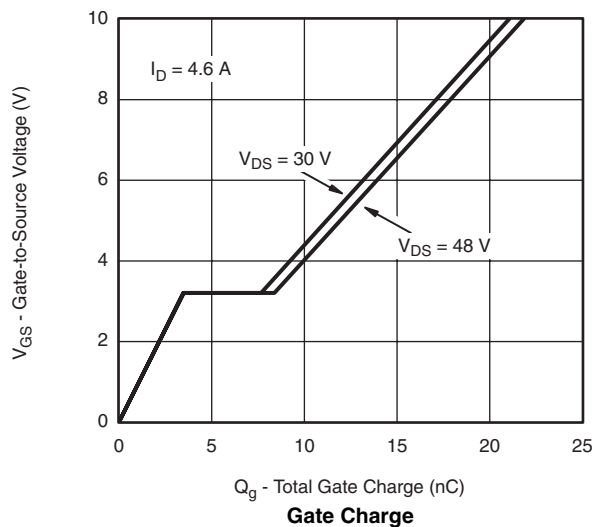
T_J - Junction Temperature (°C)
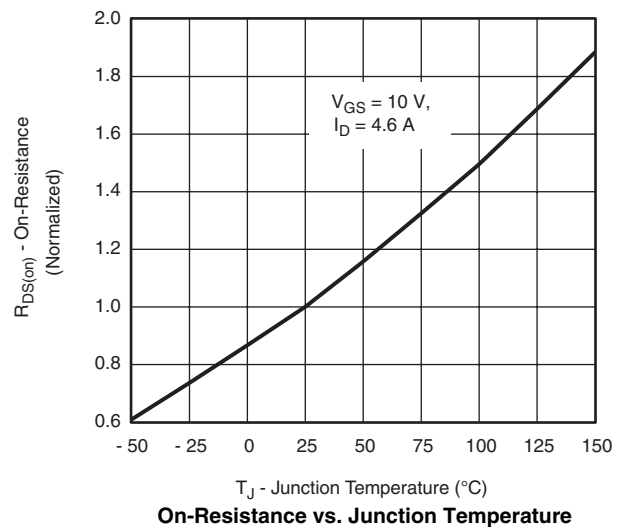
On-Resistance vs. Junction Temperature

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient

* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Current Derating*

I_D - Drain Current (A) vs T_C - Case Temperature (°C)

Package Limited

Power, Junction-to-Foot

Power (W) vs T_C - Case Temperature (°C)
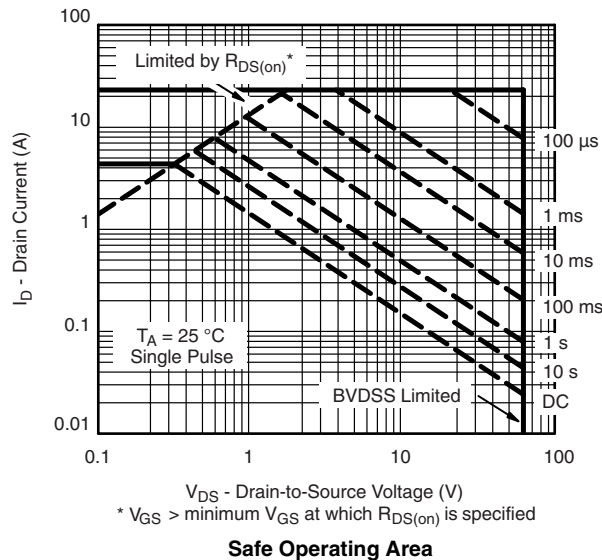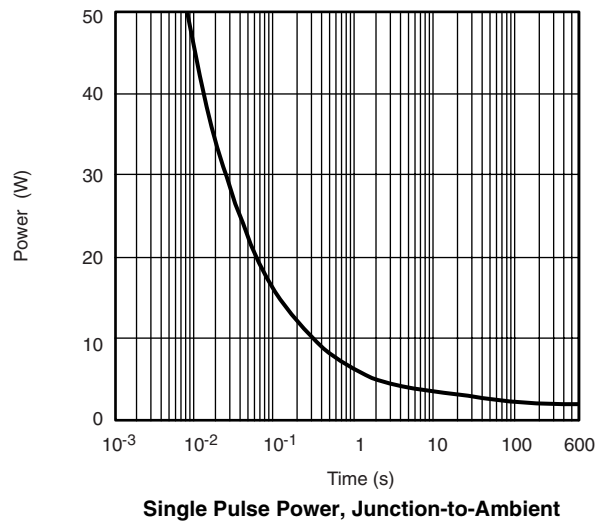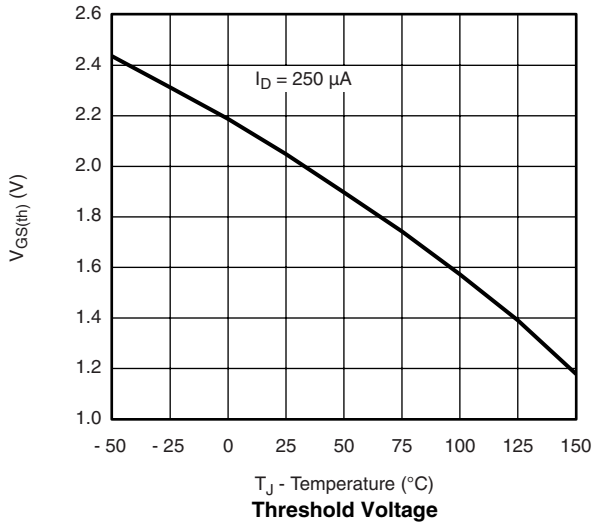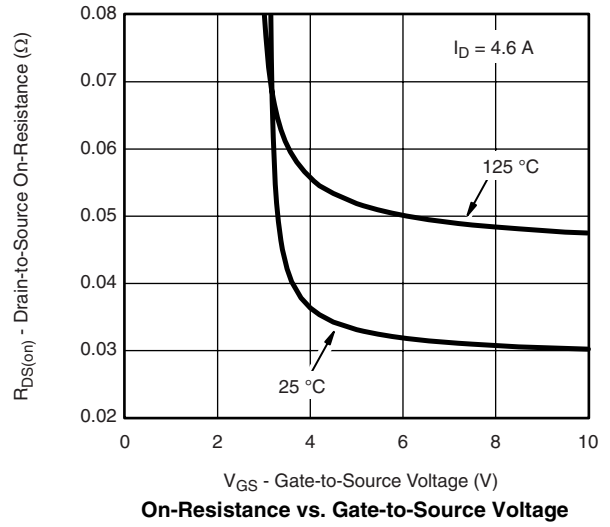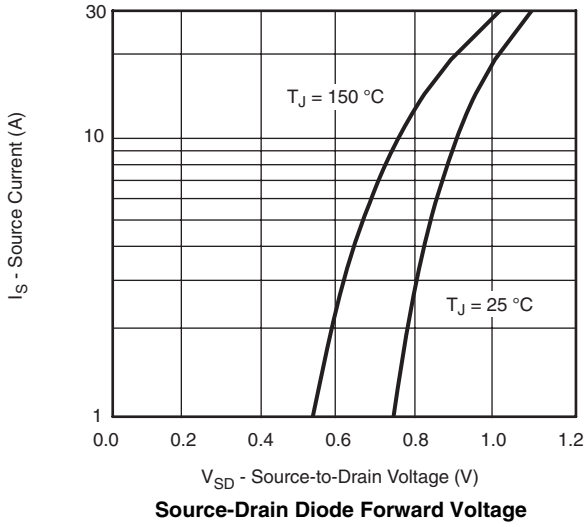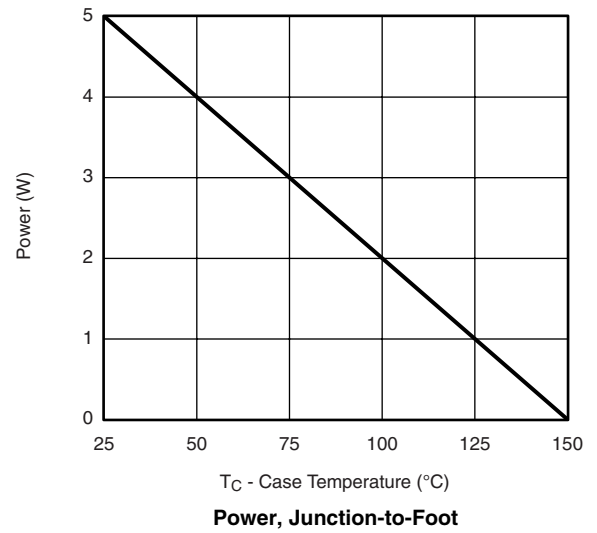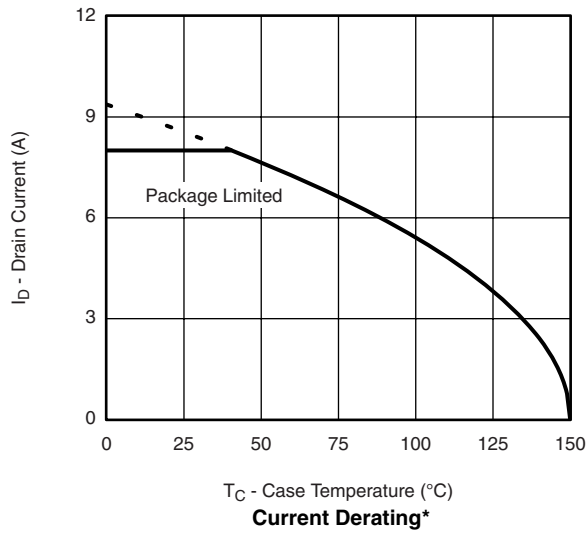
* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.
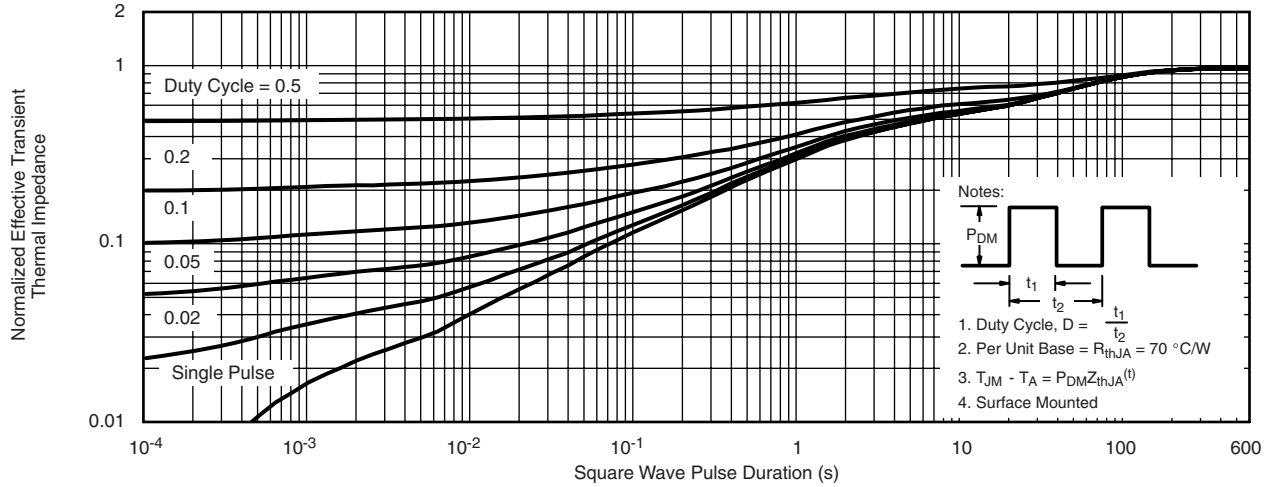
Si4436DY

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![VISHAY logo]

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Notes:

P_{DM}

t_1

t_2

1. Duty Cycle, $D = \dfrac{t_1}{t_2}$
2. Per Unit Base = R_{thJA} = 70 °C/W
3. $T_{JM} - T_A = P_{DM}Z_{thJA}^{(t)}$
4. Surface Mounted

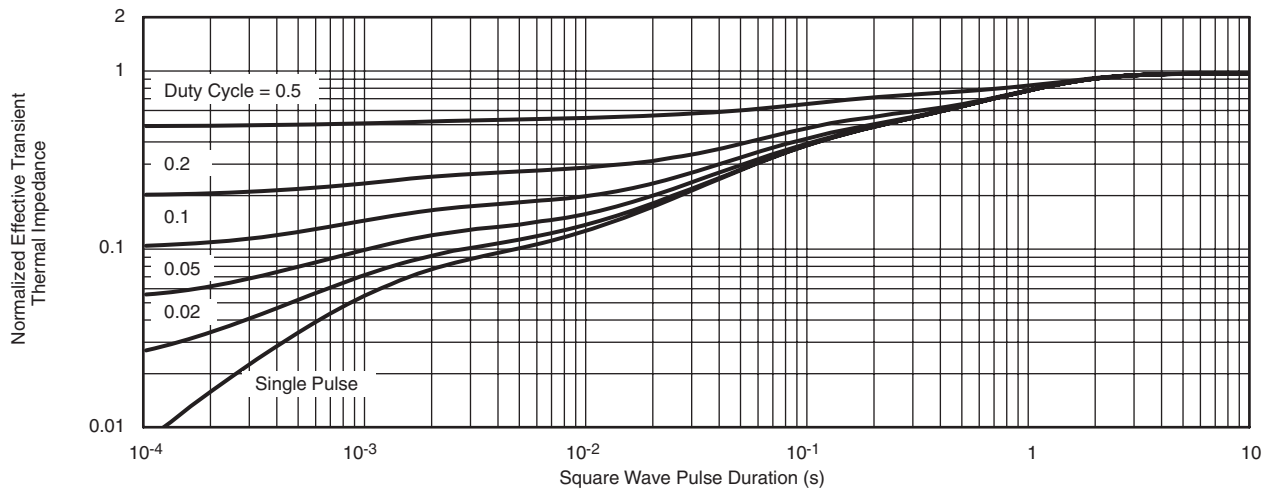Duty Cycle = 0.5

0.2

0.1

0.05

0.02

Single Pulse

Normalized Effective Transient Thermal Impedance

Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Duty Cycle = 0.5

0.2

0.1

0.05

0.02

Single Pulse

Normalized Effective Transient Thermal Impedance

Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73664.

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012

	MILLIMETERS		INCHES	
DIM	**Min**	**Max**	**Min**	**Max**
A	1.35	1.75	0.053	0.069
A$_1$	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

Mounting LITTLE FOOT®, SO-8 Power MOSFETs

Wharton McDaniel

Surface-mounted LITTLE FOOT power MOSFETs use integrated circuit and small-signal packages which have been been modified to provide the heat transfer capabilities required by power devices. Leadframe materials and design, molding compounds, and die attach materials have been changed, while the footprint of the packages remains the same.

See Application Note 826, *Recommended Minimum Pad Patterns With Outline Drawing Access for Vishay Siliconix MOSFETs,* (http://www.vishay.com/ppg?72286), for the basis of the pad design for a LITTLE FOOT SO-8 power MOSFET. In converting this recommended minimum pad to the pad set for a power MOSFET, designers must make two connections: an electrical connection and a thermal connection, to draw heat away from the package.

In the case of the SO-8 package, the thermal connections are very simple. Pins 5, 6, 7, and 8 are the drain of the MOSFET for a single MOSFET package and are connected together. In a dual package, pins 5 and 6 are one drain, and pins 7 and 8 are the other drain. For a small-signal device or integrated circuit, typical connections would be made with traces that are 0.020 inches wide. Since the drain pins serve the additional function of providing the thermal connection to the package, this level of connection is inadequate. The total cross section of the copper may be adequate to carry the current required for the application, but it presents a large thermal impedance. Also, heat spreads in a circular fashion from the heat source. In this case the drain pins are the heat sources when looking at heat spread on the PC board.

Figure 1. Single MOSFET SO-8 Pad
Pattern With Copper Spreading

Figure 2. Dual MOSFET SO-8 Pad Pattern
With Copper Spreading

The minimum recommended pad patterns for the single-MOSFET SO-8 with copper spreading (Figure 1) and dual-MOSFET SO-8 with copper spreading (Figure 2) show the starting point for utilizing the board area available for the heat-spreading copper. To create this pattern, a plane of copper overlies the drain pins. The copper plane connects the drain pins electrically, but more importantly provides planar copper to draw heat from the drain leads and start the process of spreading the heat so it can be dissipated into the ambient air. These patterns use all the available area underneath the body for this purpose.

Since surface-mounted packages are small, and reflow soldering is the most common way in which these are affixed to the PC board, "thermal" connections from the planar copper to the pads have not been used. Even if additional planar copper area is used, there should be no problems in the soldering process. The actual solder connections are defined by the solder mask openings. By combining the basic footprint with the copper plane on the drain pins, the solder mask generation occurs automatically.

A final item to keep in mind is the width of the power traces. The absolute minimum power trace width must be determined by the amount of current it has to carry. For thermal reasons, this minimum width should be at least 0.020 inches. The use of wide traces connected to the drain plane provides a low impedance path for heat to move away from the device.

APPLICATION NOTE

RECOMMENDED MINIMUM PADS FOR SO-8

Recommended Minimum Pads
Dimensions in Inches/(mm)

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